

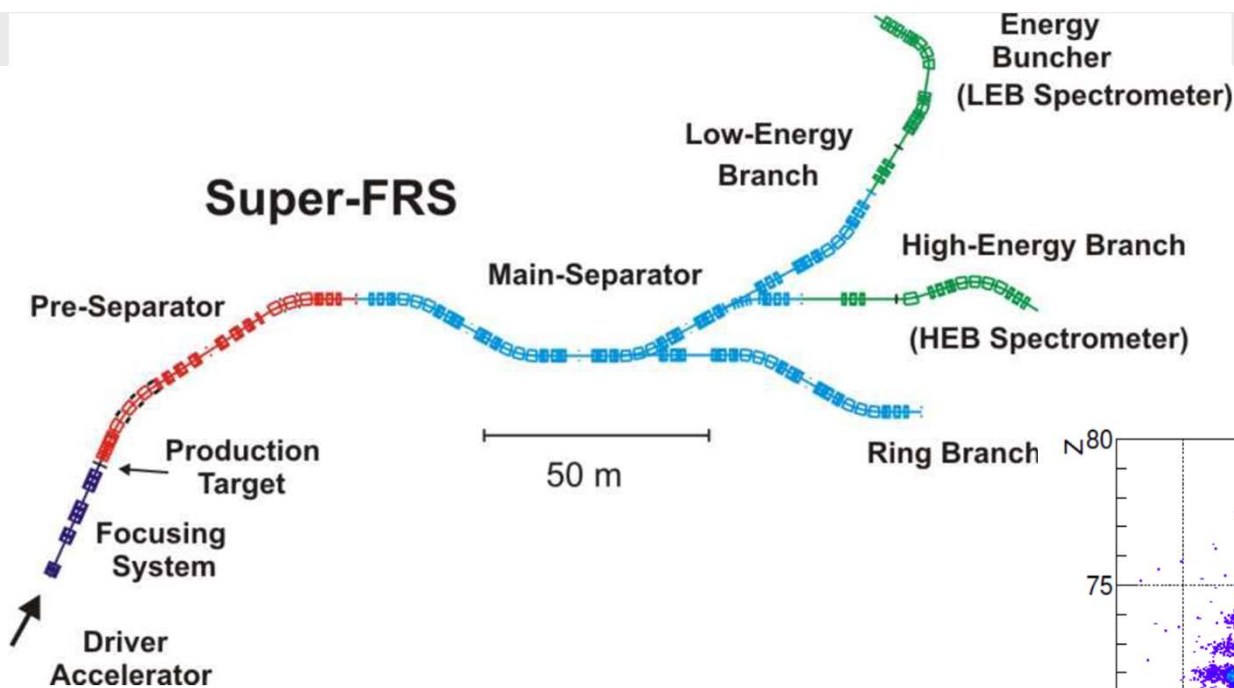
**50**  
YEARS  
GSI

# Si detectors for the TOF measurements with heavy ions

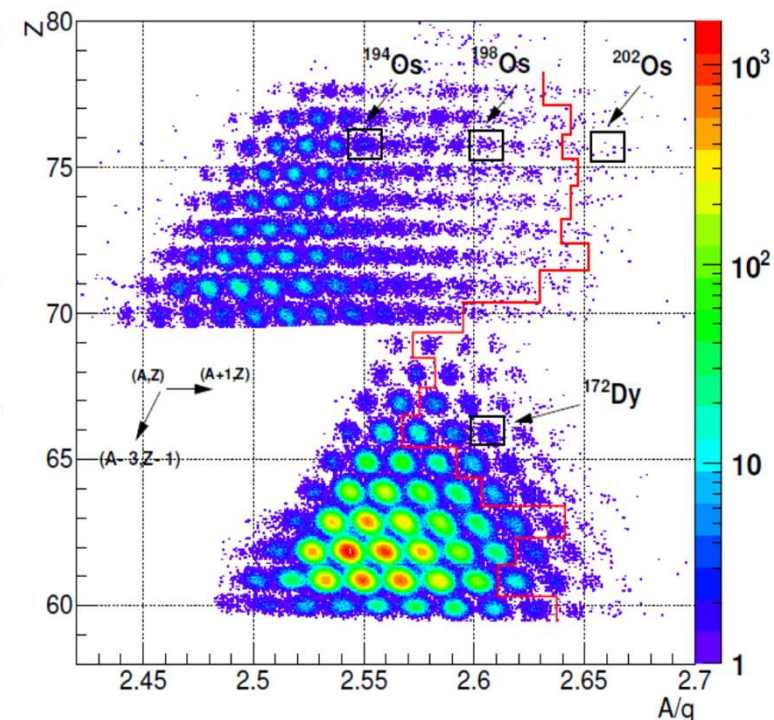
Oleg Kiselev  
GSI Darmstadt

5. annual MT meeting, Jena, 05-07.03.2019

# Particle identification @ SFRS FAIR



- Beam diagnostics –  $\Delta E$  –  $ToF$  (Time of Flight) method
- The simultaneous measurements of the energy loss and the time of flight can **uniquely identify the particles**
- Rate from  $10^{12} \text{ s}^{-1}$  at pre-separator to  $10^5 \text{ s}^{-1}$  at the end of main separator

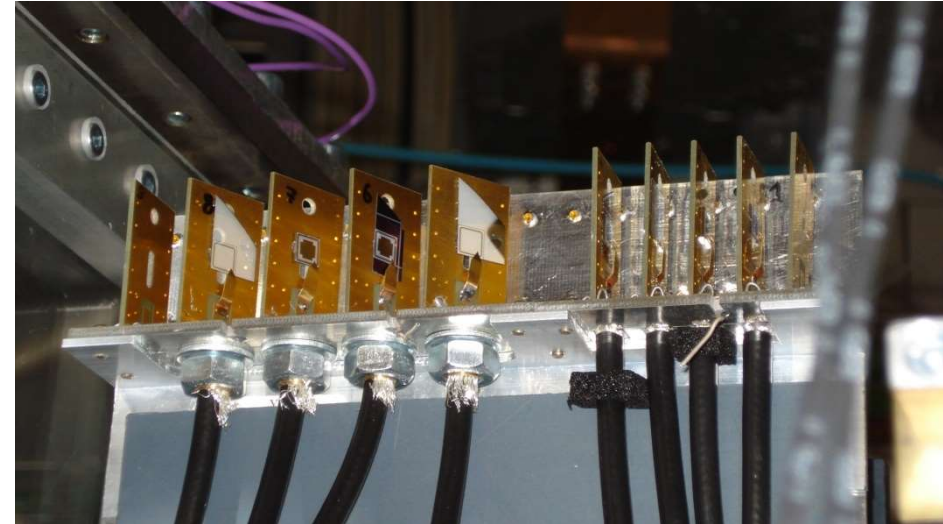
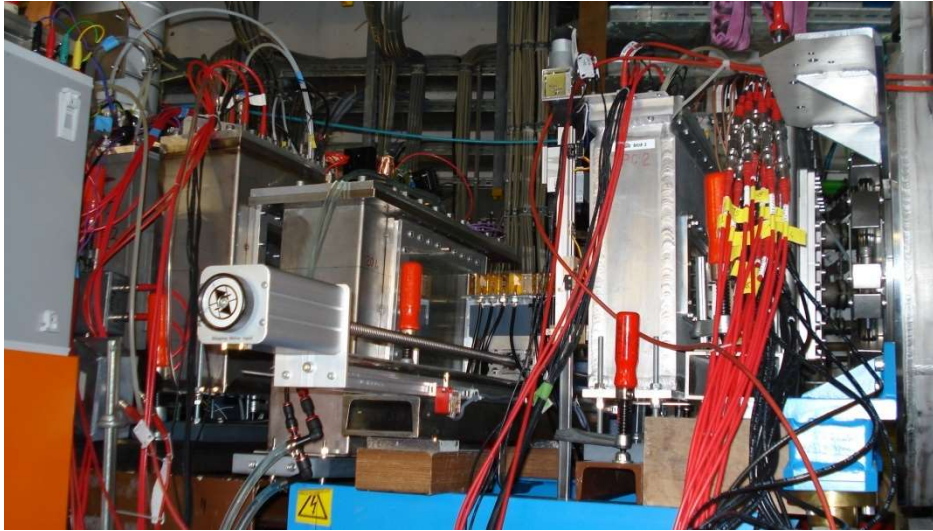


[F.Farinon, JLU Gießen, Diss., 2012]

# Si detectors for TOF

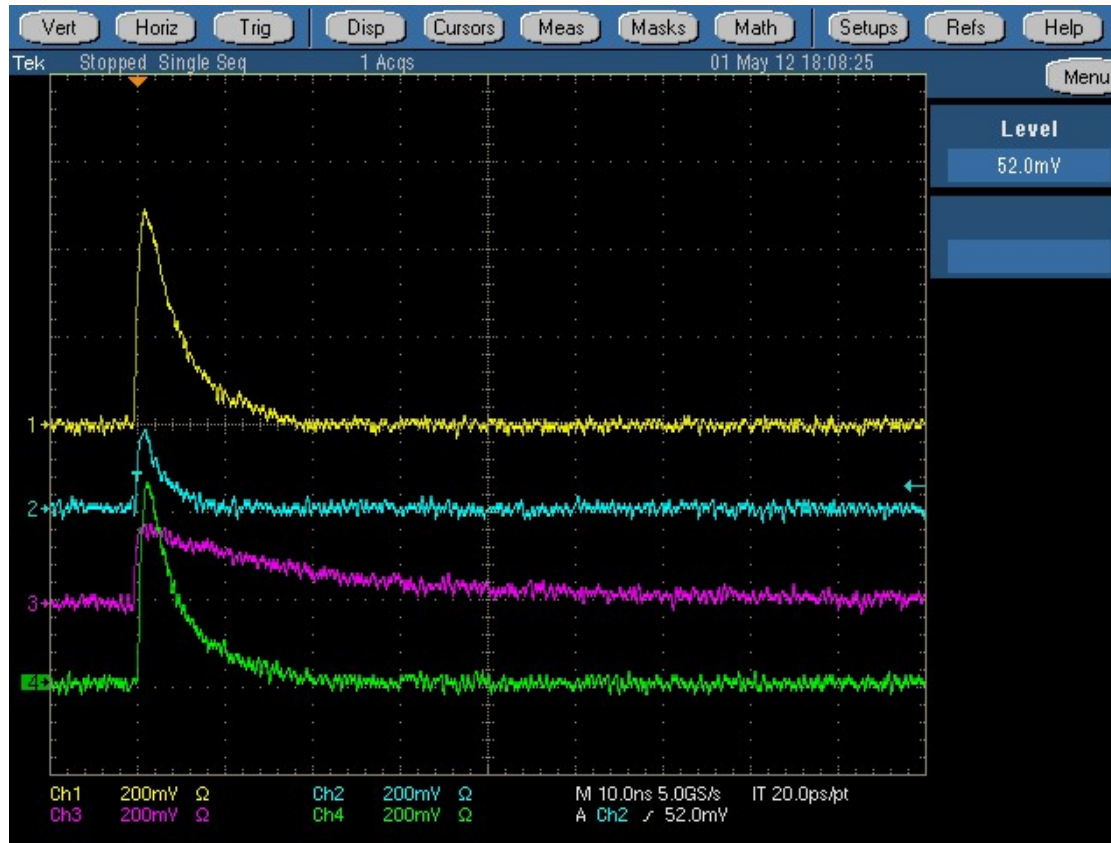
- Si detectors typically used for energy measurements and tracking only – slow??
- Matter of proper detector topology and electronics
- Proposal to use Si strip detectors for TOF stations MF4, MF7, MF11
- Ion rate  $<10^5 \text{ s}^{-1}$  per station
- Time resolution  $< 50 \text{ ps}$
- Position resolution – 0.1 – 1 mm
- Fast trigger for the rest of the diagnostic system
- Feasibility needs to be demonstrated

# First test experiment at FRS



- Beam –  $^{197}\text{Au}$  at 750 MeV/u
- S2 focal point of the FRS
- 8 Si detectors
- Size – 25 mm<sup>2</sup>, matched to capacity to a typical size and capacity of one strip of large strip detector
- Readout directly from the detectors with a fast oscilloscope (4 GHz bandwidth, 8 bit, 10 GS/s)

# Example of the digitized signals



***No amplification!***

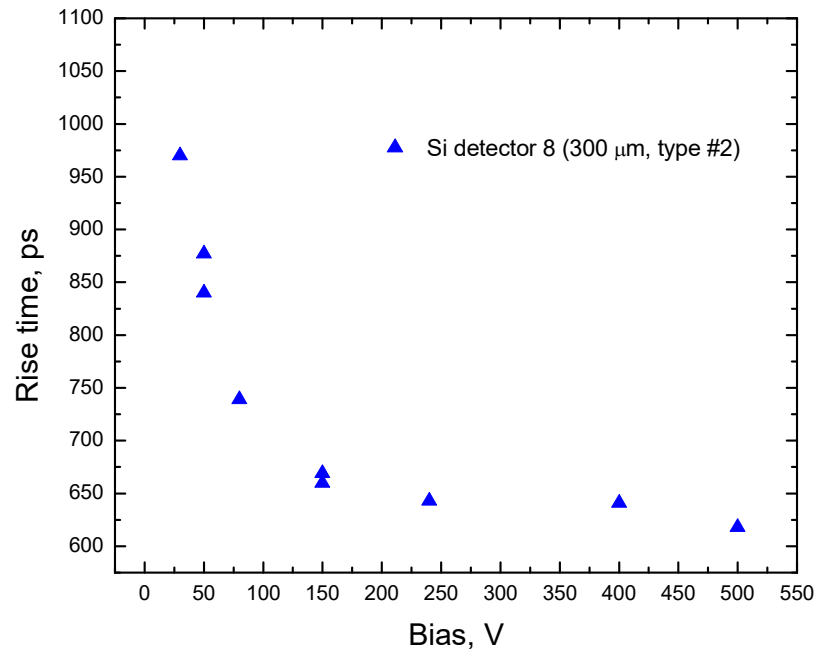
Waveforms saved and analysed offline

Waveform analysis software developed specially for the project

Amplitude, charge, rise time, time and charge correlations extracted



# Rise time vs bias, detector #8



*Time resolution in first order directly proportional to the slope of the signal and inverse proportional to the noise*

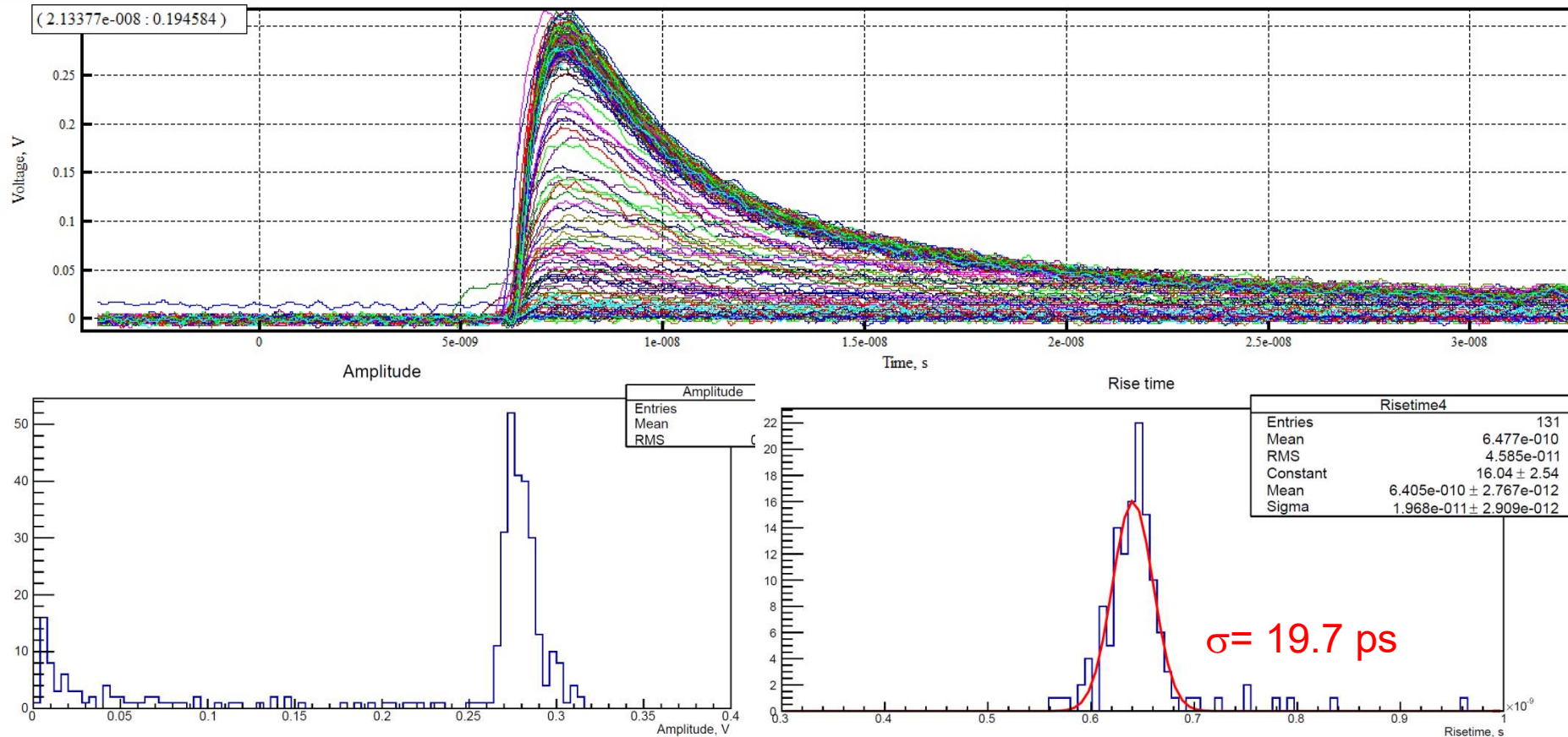
*So – fast and strong signals are important*

Thickness 300  $\mu\text{m}$ , type #2

Rotated to  $30^\circ$  with respect to beam axis

Good resolution (20 ps) start from 150 V

# Time jitter with pulse-shape analysis



Time jitter obtained using leading-edge discriminator with amplitude correction

**Using CFD might provide even better timing**



# PADI amplifier/discriminator + FPGA TDC

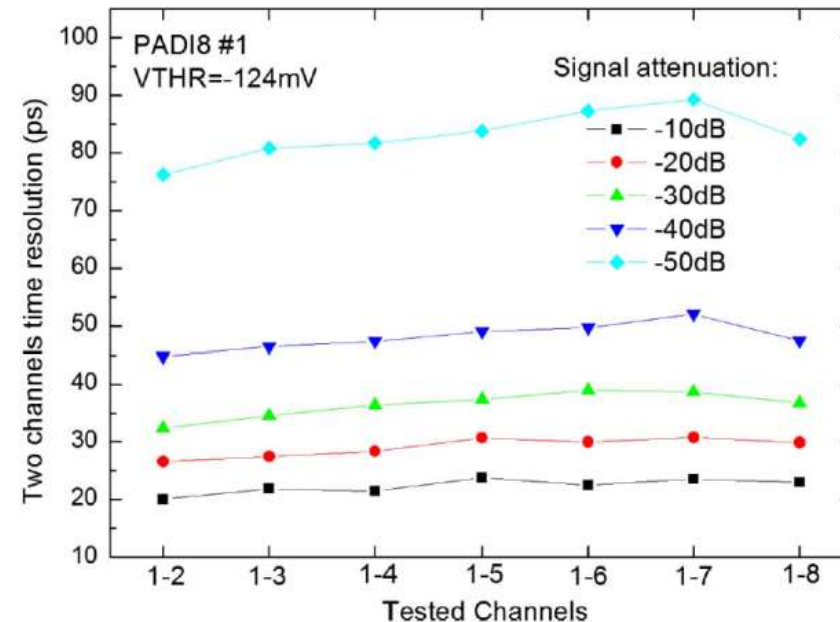


Fig. 19. Measured time resolution for different channel combinations on one chip (channel 1 against the others 7). The test pulse (0.25 V amplitude and 3 ns width) is attenuated by the specified values.

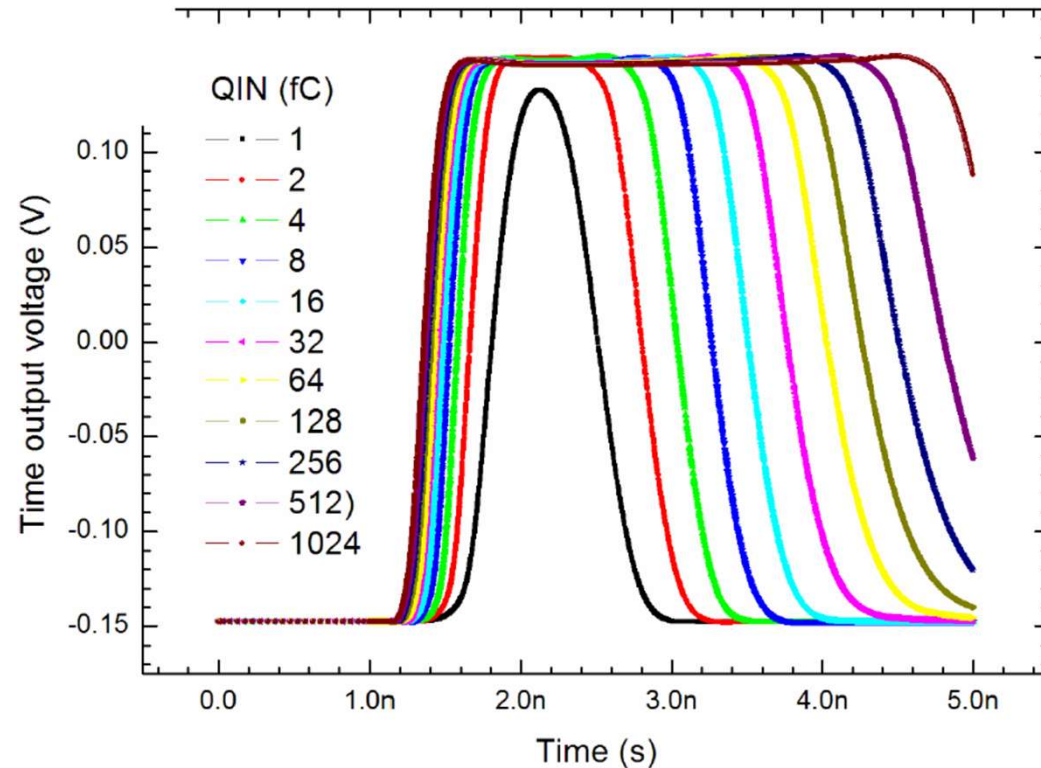
## GSI DL and ExEI

- ASIC developed at for extremely fast signals and best possible time resolution
- 4/8 channels per chip – **current amplifier** (x100) and leading-edge discriminator, Time-over-Threshold, LVDS output
- VFTX2 FPGA TDC – 28 channels with 7 ps time resolution (GSI development)



# PADI8 ASIC

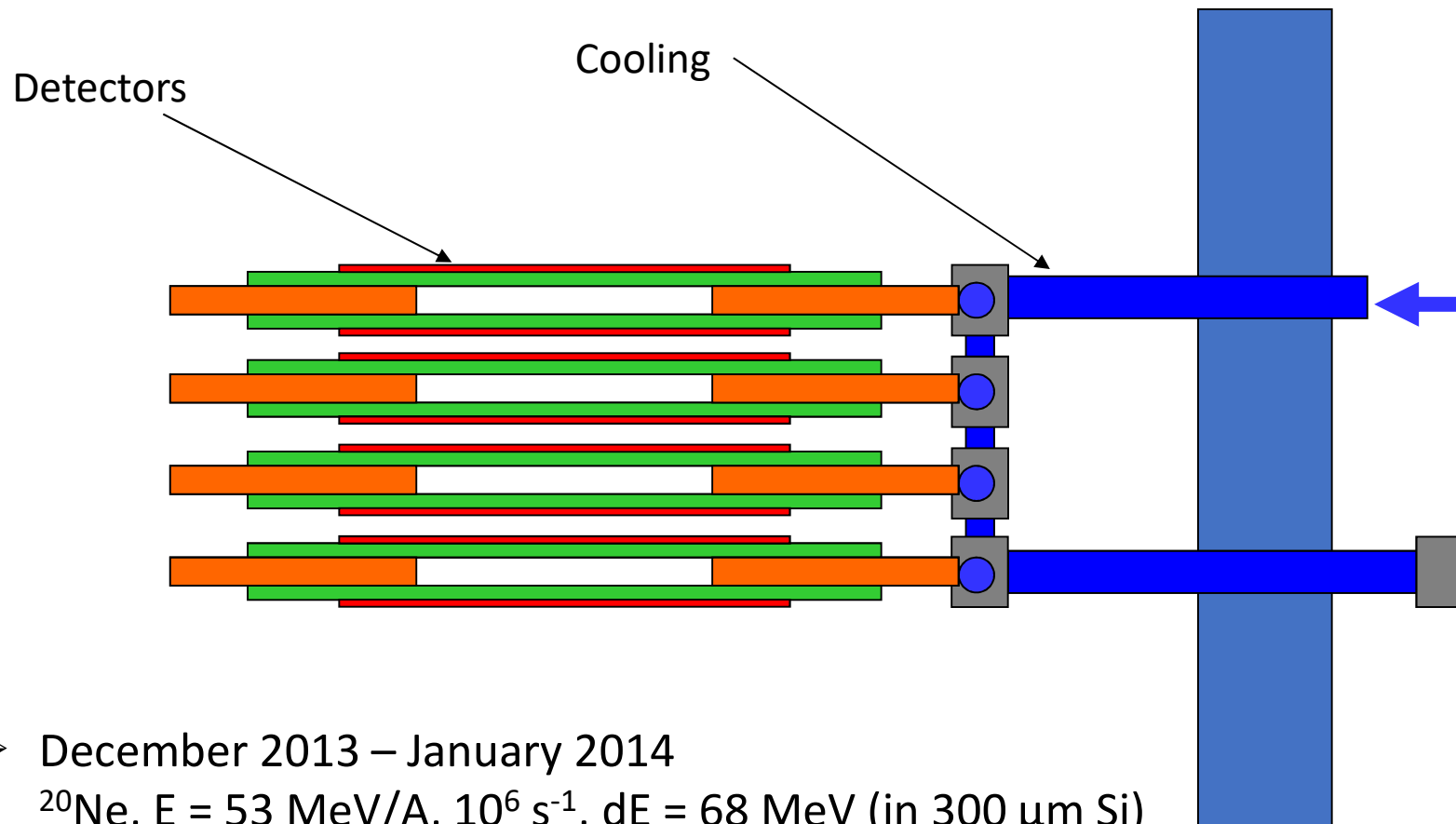
- UMC 180 nm
- 8 channels
- One threshold per channel
- Time and ToT
- Bandwidth 400 MHz
- Peaking time 1 ns
- Equivalent noise 1145 e<sup>-</sup>
- Power consumption 17 mW/ch



## ***GSI DL and ExEI***

*M. Ciobanu et al., IEEE Transaction on Nuclear Science,  
V 61, N 2 (2014) 1015*

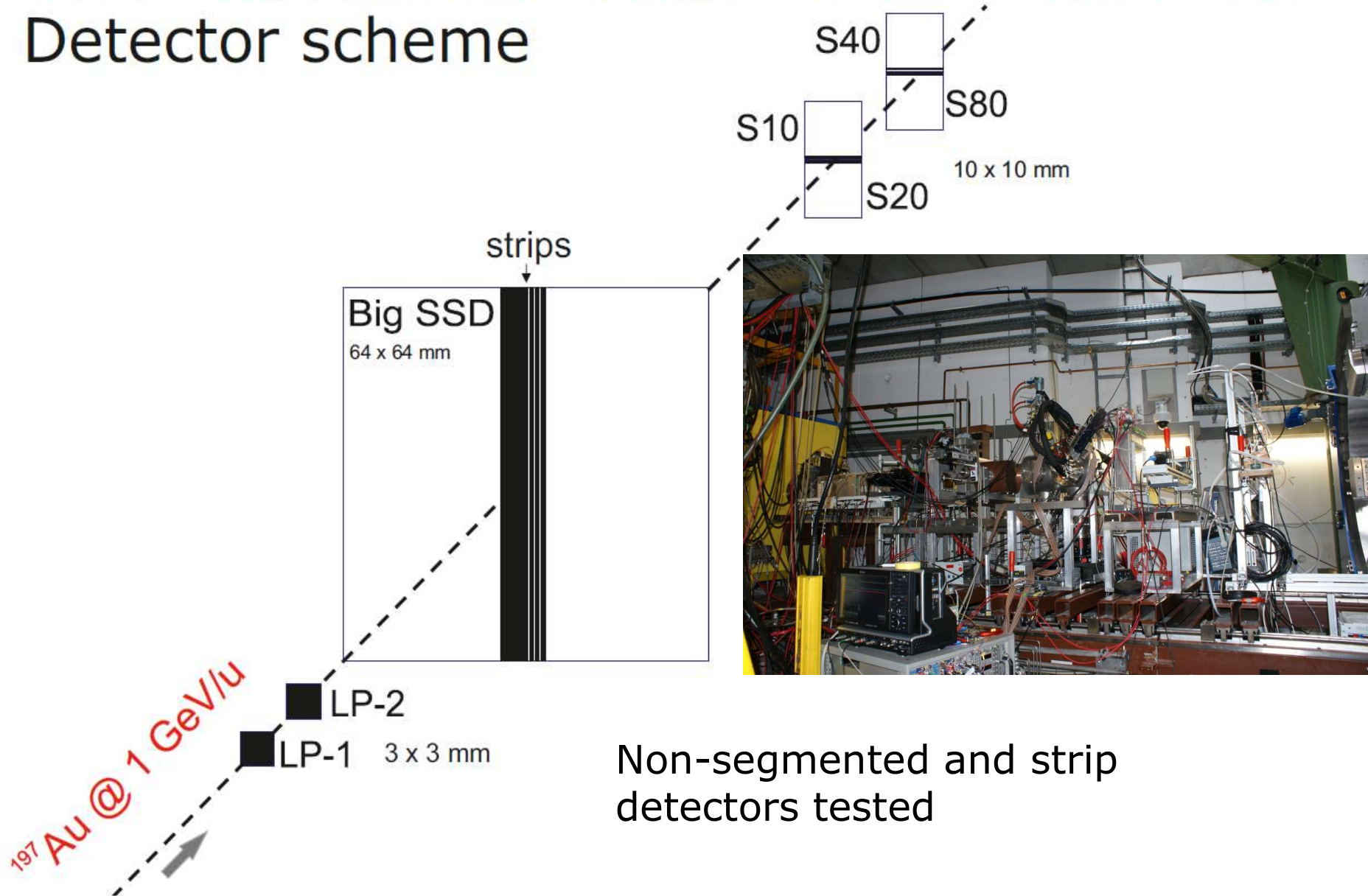
# Detectors for the beam tests at JINR, Dubna



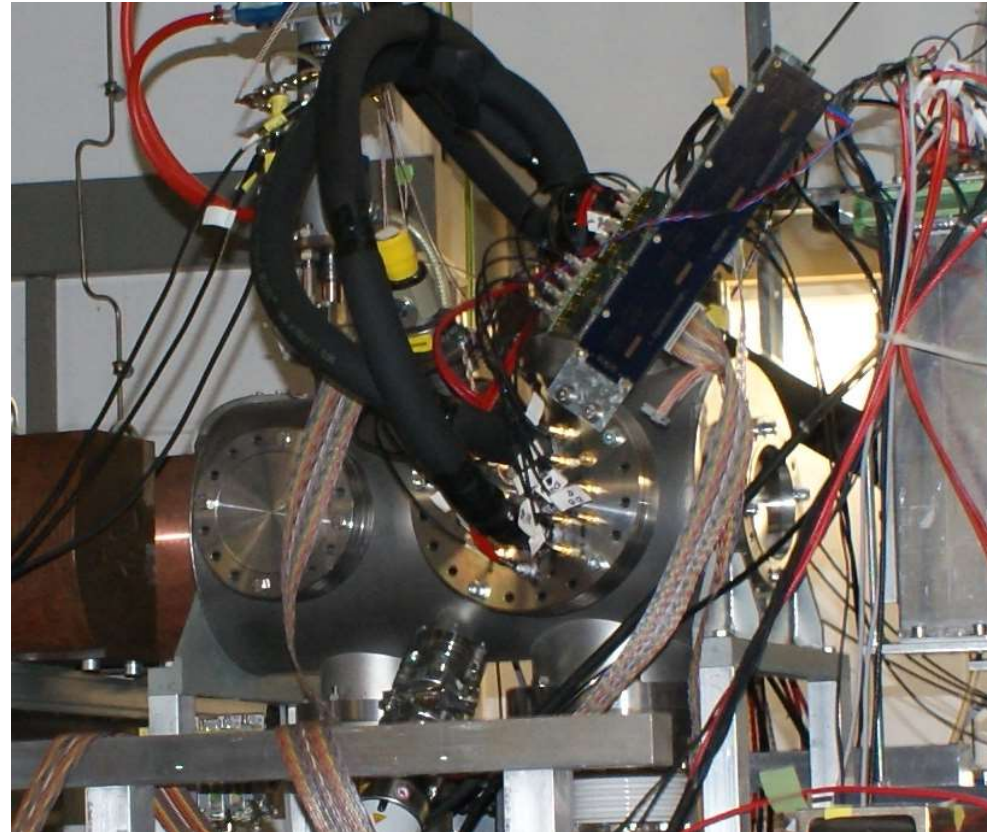
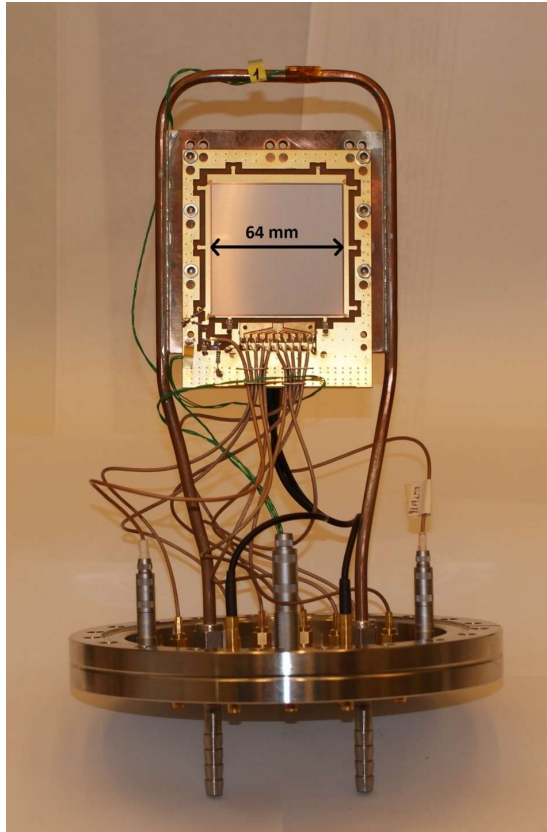
- December 2013 – January 2014
  - $^{20}\text{Ne}$ ,  $E = 53 \text{ MeV/A}$ ,  $10^6 \text{ s}^{-1}$ ,  $dE = 68 \text{ MeV}$  (in  $300 \mu\text{m Si}$ )
  - $^{11}\text{B}$ ,  $E = 35 \text{ MeV/A}$ ,  $10^6 \text{ s}^{-1}$ ,  $dE = 24 \text{ MeV}$  (in  $300 \mu\text{m Si}$ )
- Several detectors in stack, size – up to  $64 \times 64 \text{ mm}$
- Cooling up to  $-30^\circ$ , in vacuum chamber

# Test experiment Aug. 2014 @ FRS GSI

## Detector scheme



# Cooled detectors in a vacuum chamber



- The temperature of cooling tube  $-13^{\circ}\text{C}$ , detectors  $+7^{\circ}\text{C}$
- Cooling of the detectors is reducing dark current and noise
- Vacuum about  $10^{-4}$  mbar
- Diamond detectors in the same vacuum chamber

# 4 different versions of DAQ

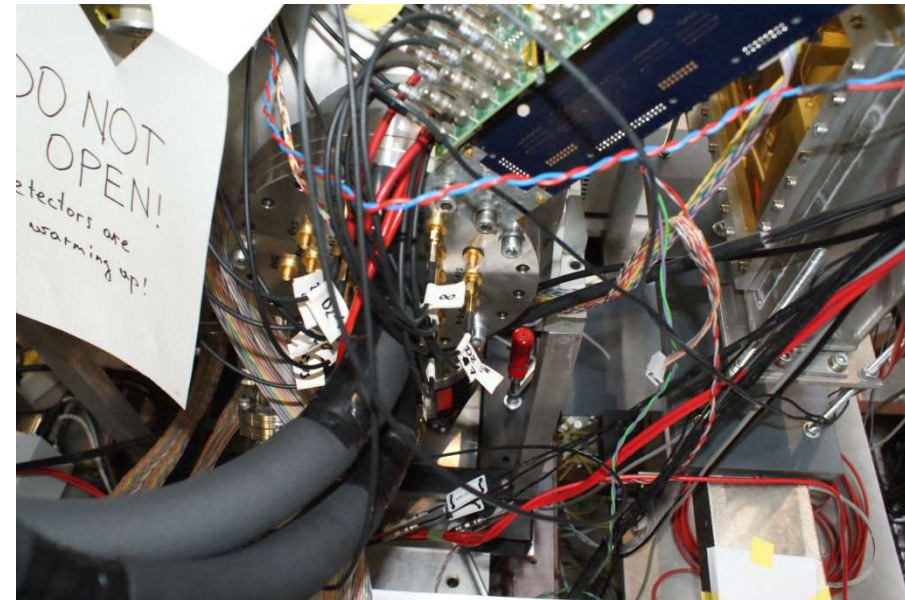
- Fast oscilloscope with 2 GHz analog bandwidth
- PADI preamplifier/discriminator + VFTX2 TDC
- CAEN FADC DT5742, sampling up to 5 Gs/s
- CAEN FADC DT5743, sampling up to 3.2 Gs/s, **beta-test of the device and the software (special deal with CAEN)**



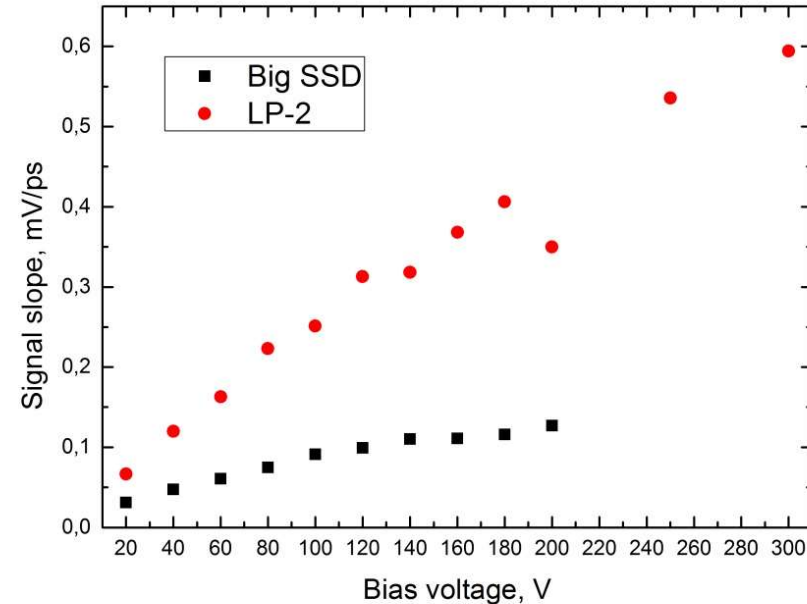
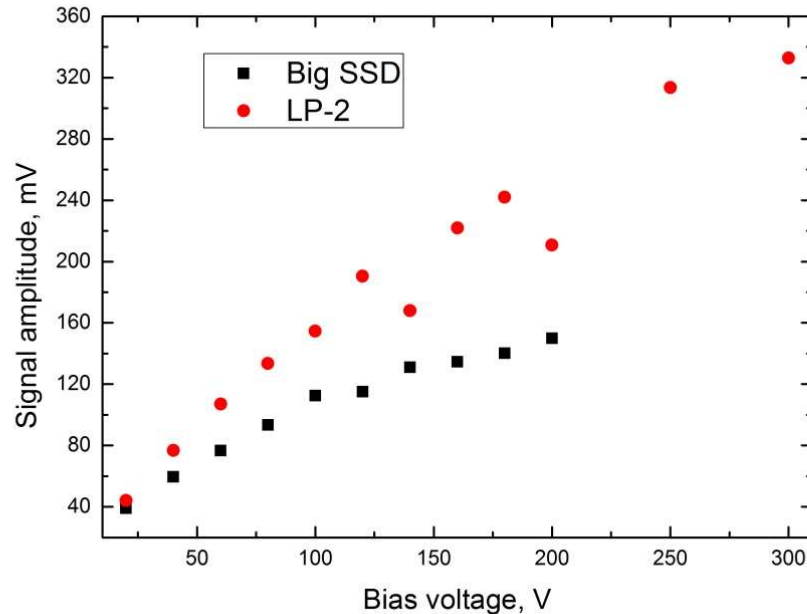
DT5743



DT5742



# Signals vs bias



Optimum bias for all detectors found in this way

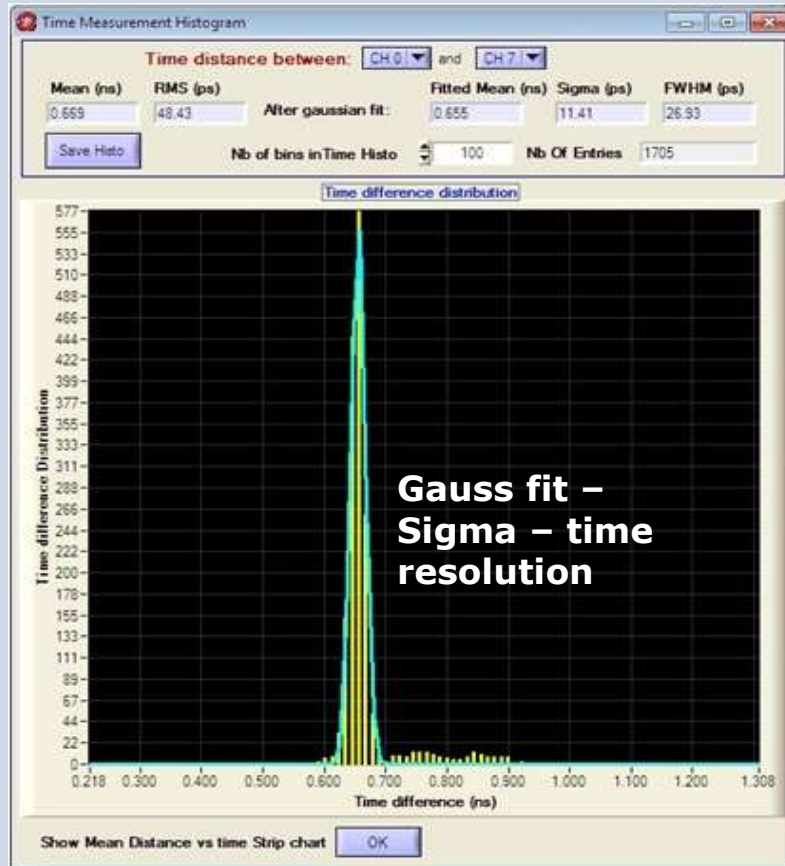
In order to get good timing, the detectors need to be overbiased  
(and have low dark current)

# Time resolution with FADC and PADI/VFTX

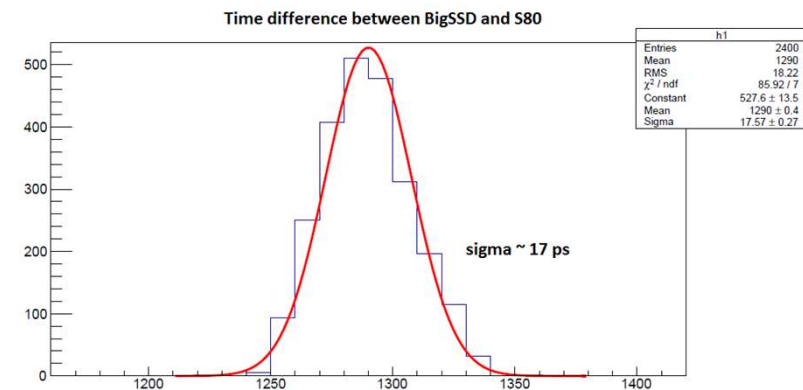
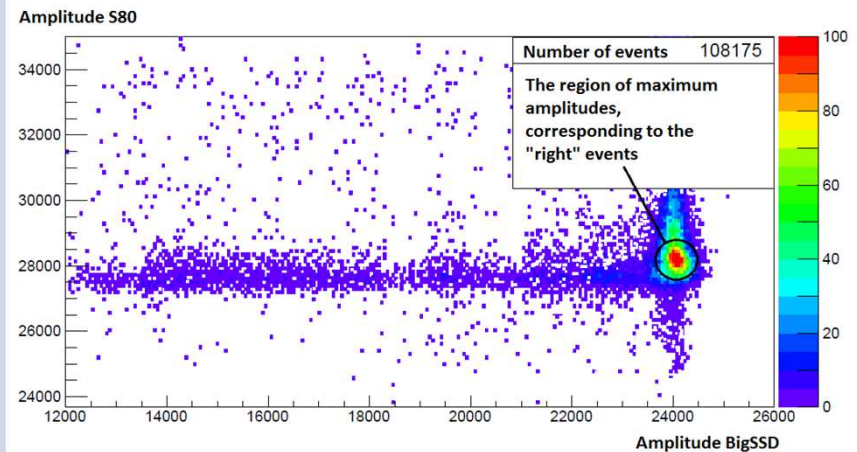


## DT5743

CAEN WaveCatcher, built-in CFD method



## PADI + VFTX



# Results of this test

Detector pair	PADI + VFTX2, $\sigma$ (ps)	DT5743, $\sigma$ (ps)
big SSD and S80	17	15
big SSD and S20	16	60

The results obtained with PADI + VFTX2 (sigma  $\sim$  17 ps) look more stable for all combination of the detectors. This testifies **the perspectives of use** of the radiation hard silicon strip detectors for the beam diagnostics in the RIBs experiments.

*There is the difference of time resolution for different detector pairs in case of DT5743 analysis. The low sampling frequency (bin 312.5 ps) or specific algorithm of smoothing procedure??*



# Test experiment June 2016, Cave C GSI

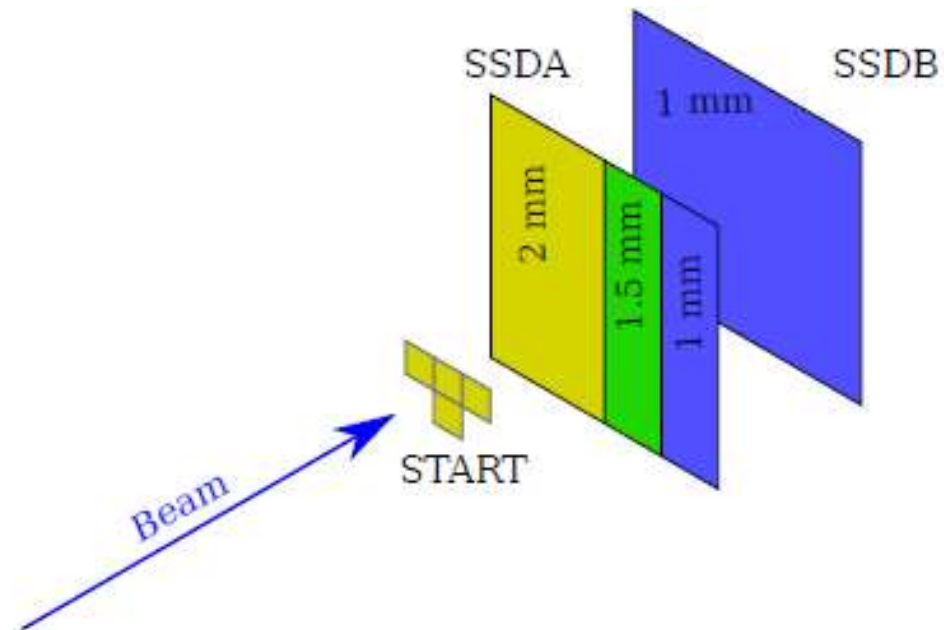
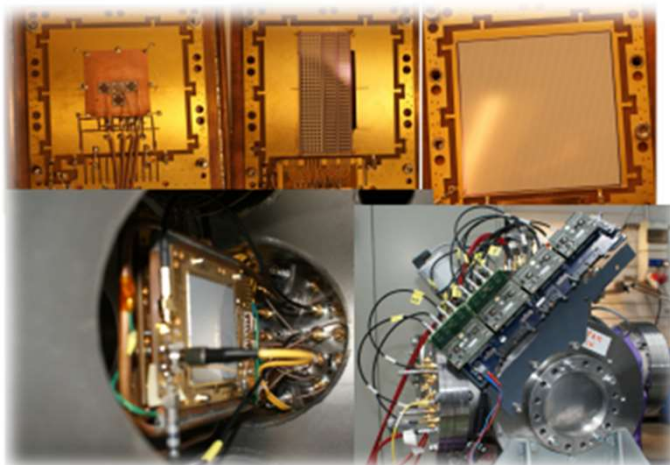


## Detectors:

- 4 5x5 mm 300  $\mu\text{m}$  non-segmented detectors
- 64x64 mm 300  $\mu\text{m}$  strip-detector with different strip size (2, 1.5 and 1 mm)
- 64x64 mm 300  $\mu\text{m}$  strip-detector with 1 mm strips

## Readout systems:

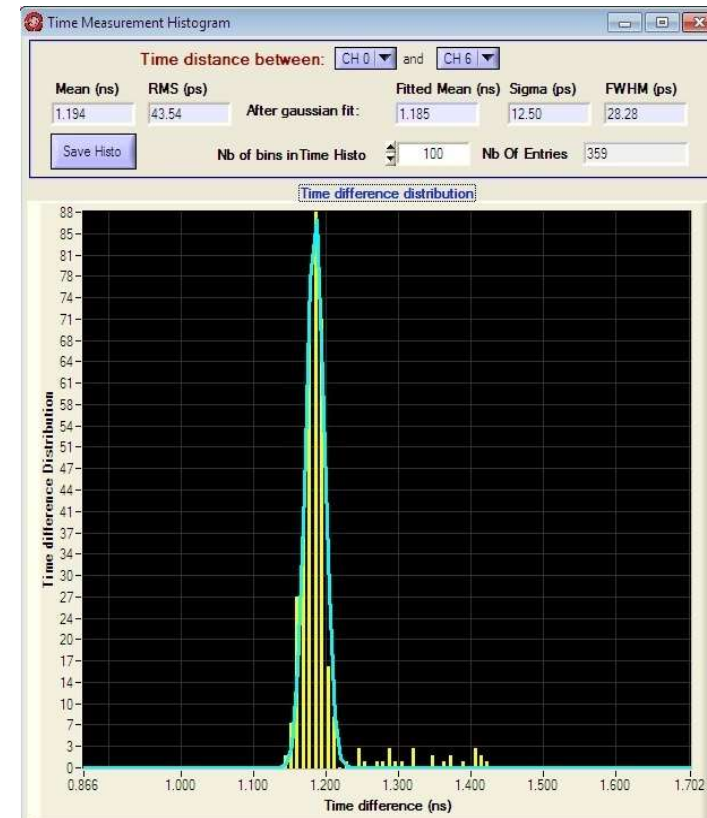
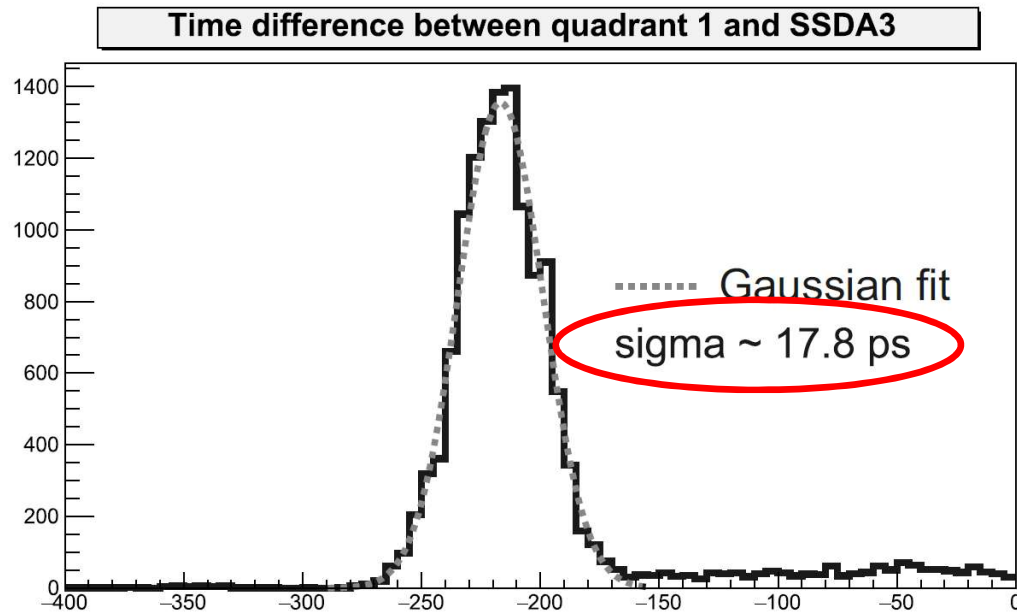
- PADI + VFTX2
- 32 ch Mesytec QDC



# Time resolution, test experiment June 2016



- Xe beam 600 MeV/u

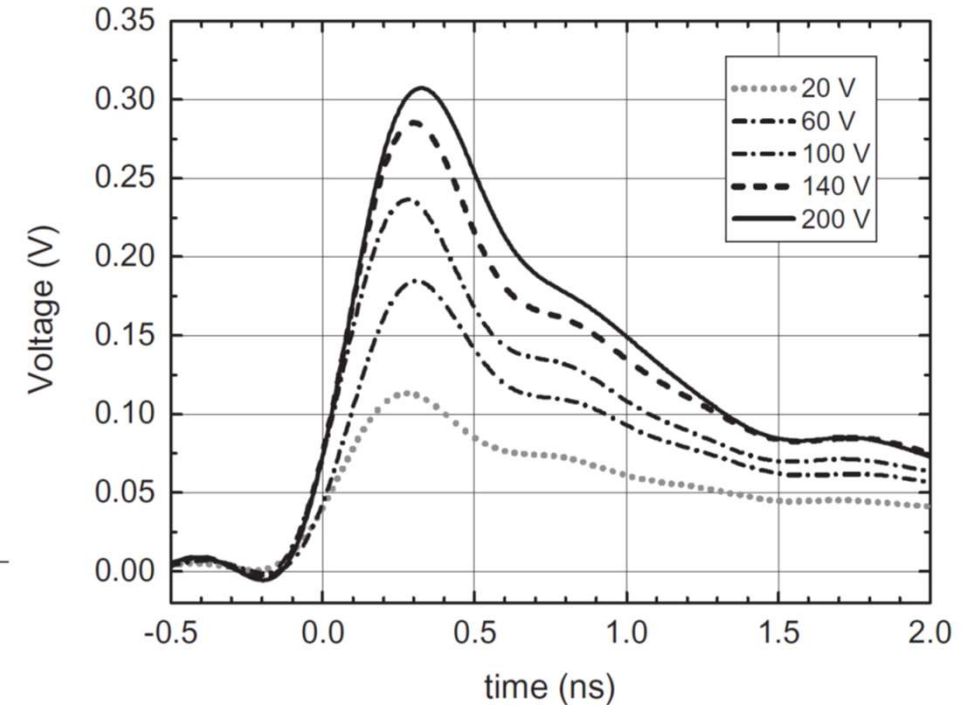
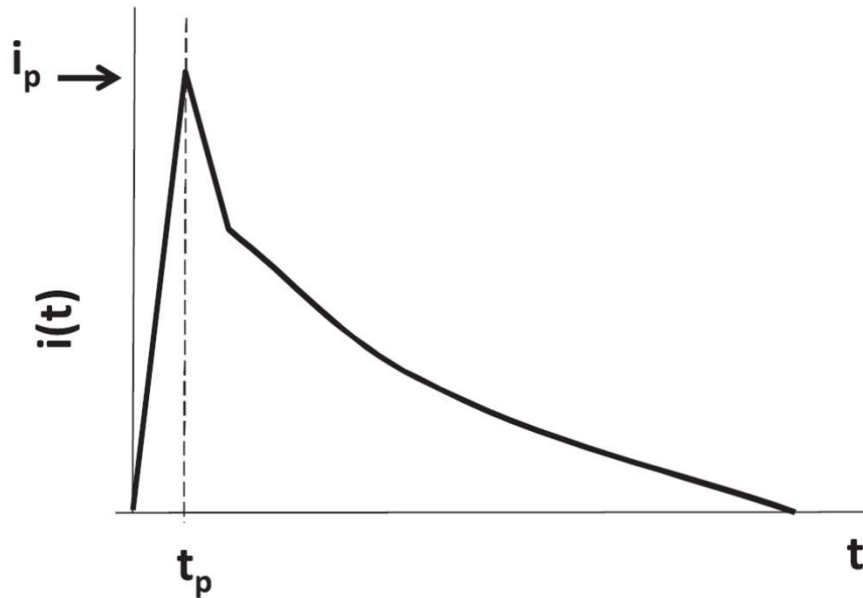


[V. Eremin et al. JINST 12 C030001 2017]

- Time resolution for C beam 600 MeV/u ~100 ps



# Simulation of current response/timing



$T_p \sim 20$  ps

Rise time of the real signal from the detector 200-1000 ps,  
defined by the RC and bandwidth of the amplifier/digitizer

*V. Eremin, O. Kiselev et al., NIM A796 (2015) 158*

# Simulation of the signals produced by the heavy ions



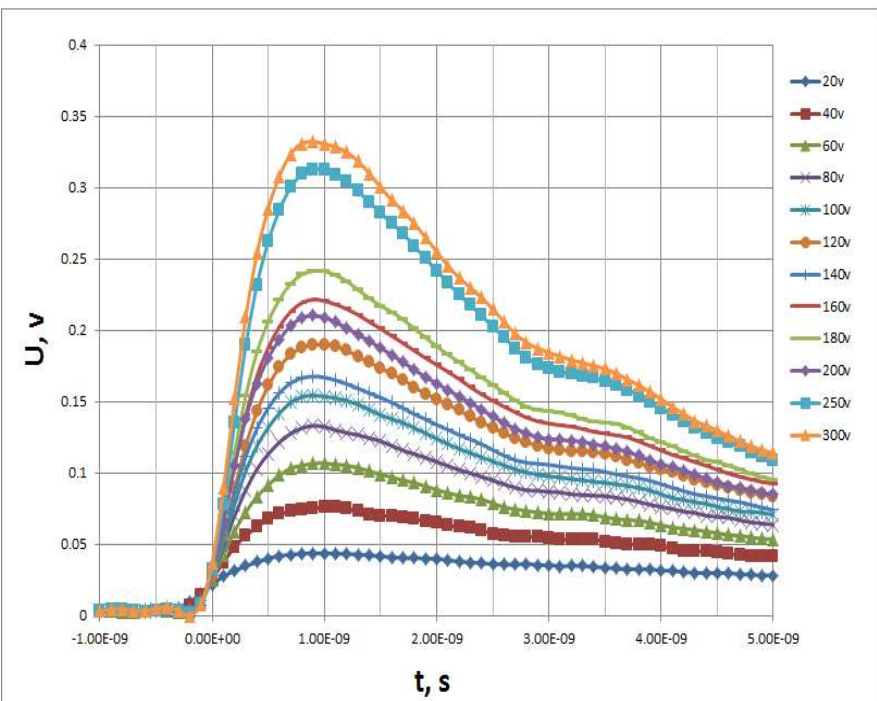
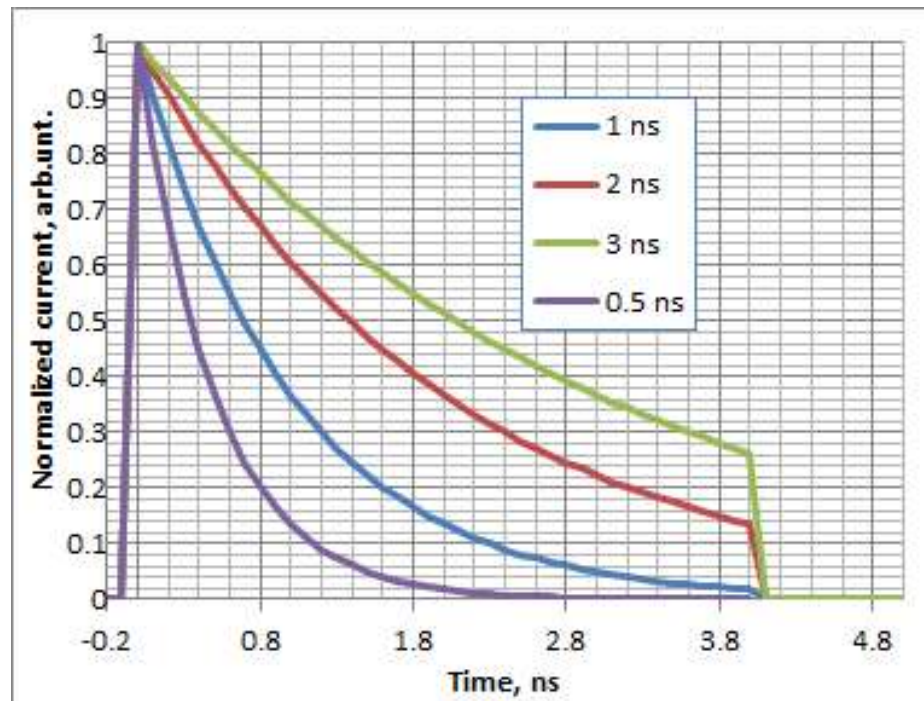
Rising edge of current pulses

$^{197}\text{Au}$ ,  $E = 920 \text{ MeV/u}$

Detector thickness - 300  $\mu\text{m}$

Voltage range 20 – 300 V

Simulated current pulses at different trapping time



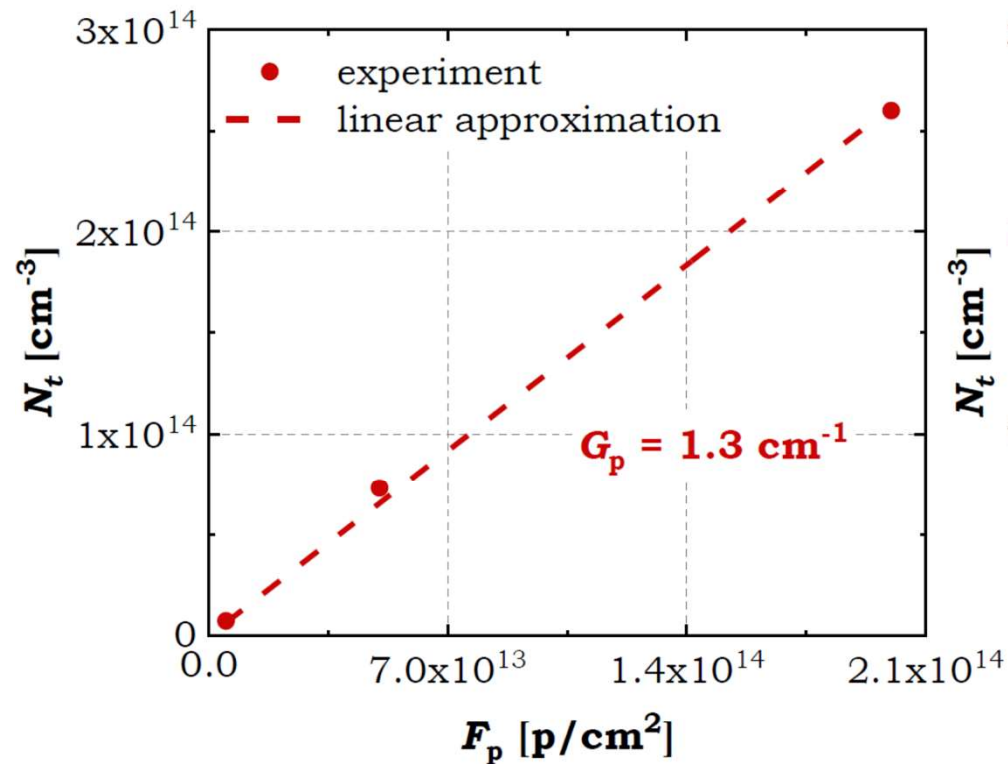
Amplitude of the peak current  $I_p$

$I_p$  at  $1e^{12} \text{ ions/cm}^2 = 1 - Tr/Ttr = 1 - 1\text{ns}/5\text{ns} = 0.8$  (1ns – time of reaching maximum)

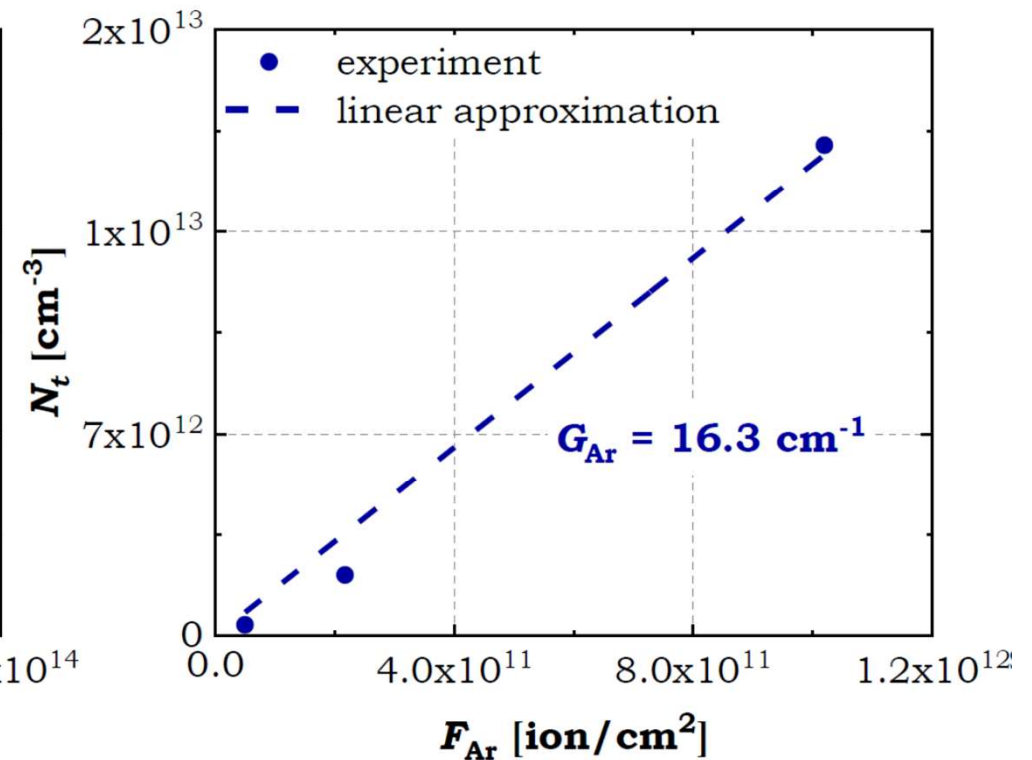


# Radiation damage – introduction rate

## protons



## <sup>40</sup>Ar ions

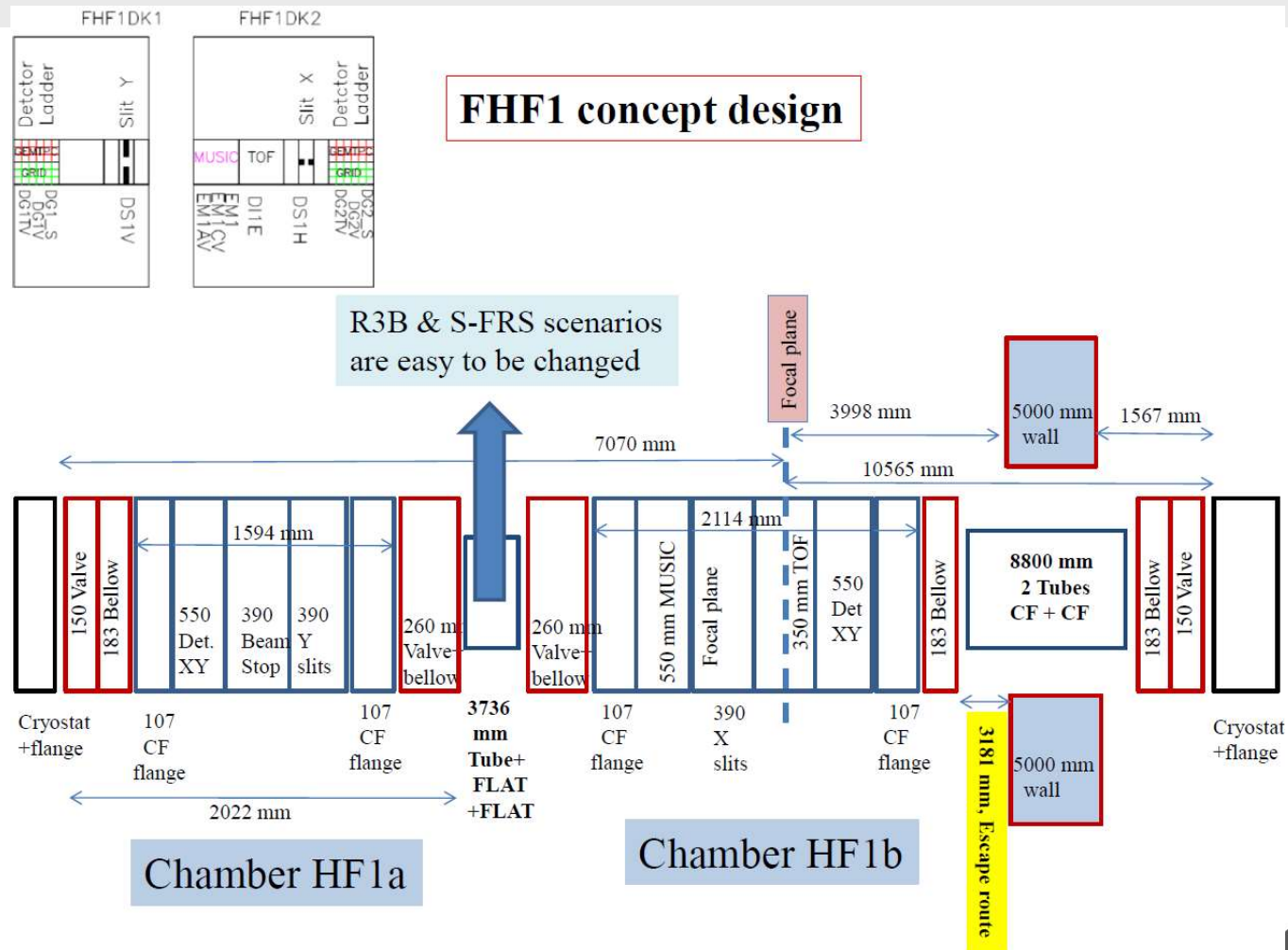


**Ions/proton ratio ~11!**



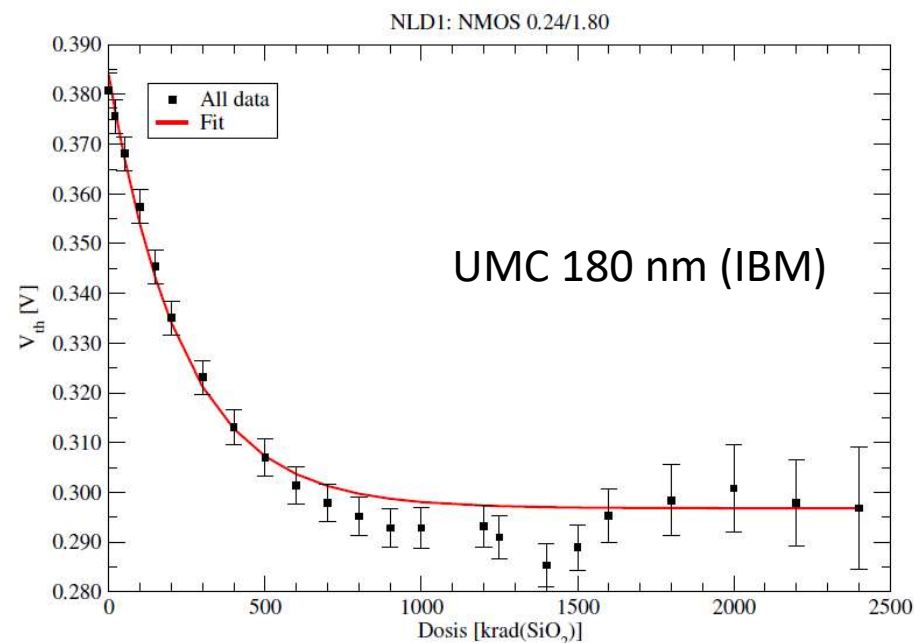
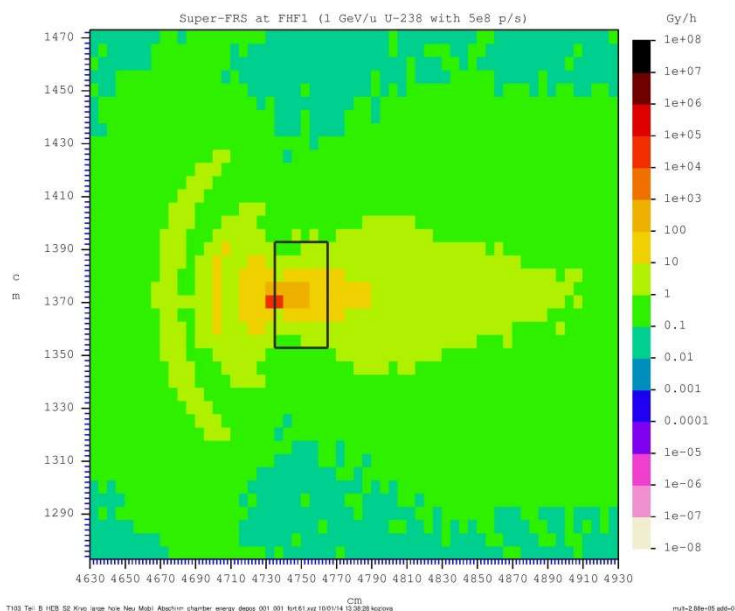
*D. Mitina et al., 33 RD50 Workshop, CERN, Geneva, Nov 26-28, 2018*

# TOF detectors at SFRS (FHF1)



- Limited space, vacuum, active cooling
- Mounting on a movable ladder

# TOF detectors at SFRS – rad. dose



- 100 Rad/h at the position of FEE  $\Rightarrow$  Mrad/month (worse case)
- FEE should be rad. hard at Mrad level
- Location of FEE – better 10-20 cm from the beam if possible

Fig. 5. Threshold voltage shift of a single NMOS transistor (0.24/1.80) for different dose levels.

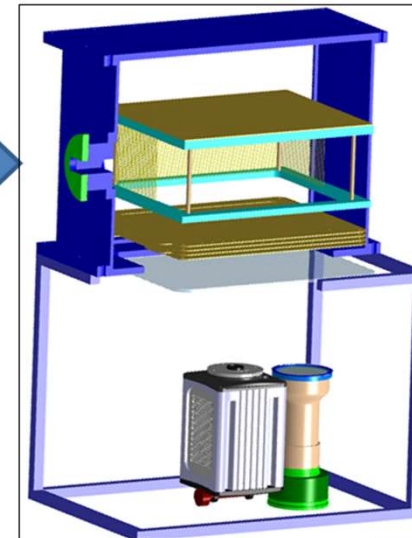
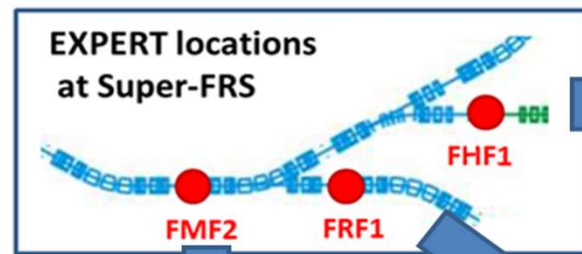
*S. Löchner, Proceedings of European Conference on Radiation and Its Effects on Components and Systems (RADECS), IEEE, 2009*

*Published data - 130 nm BiCMOS and CMOS are rad. hard up to several MRad*

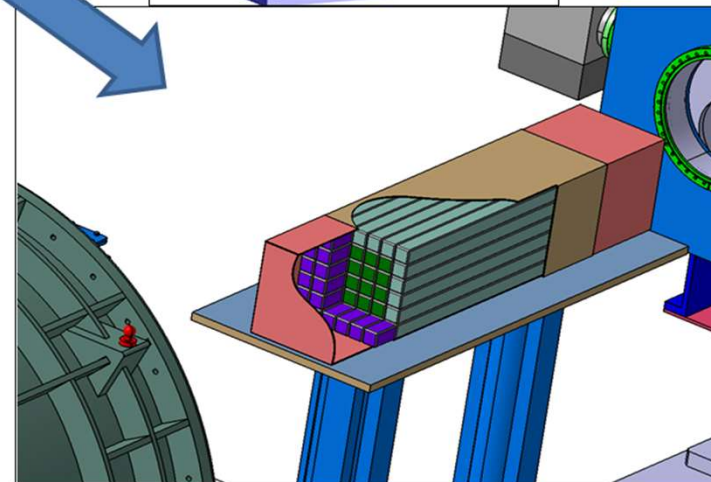
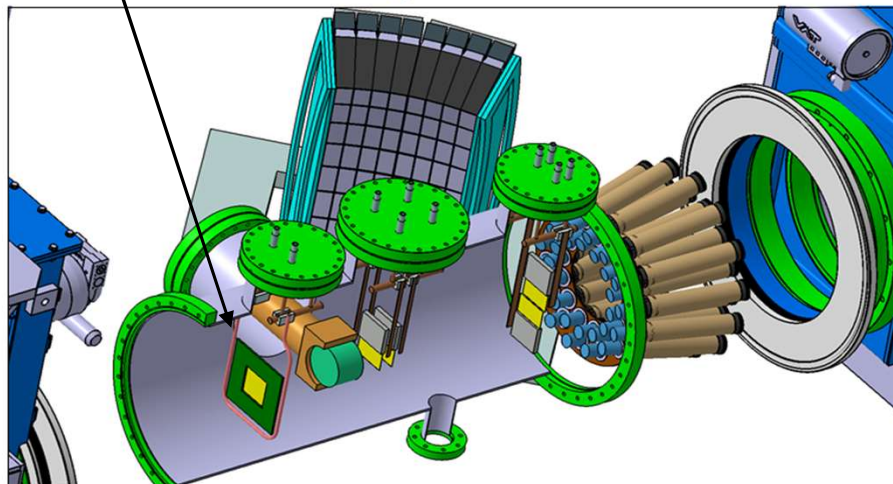


# Detectors EXPERT at different locations

## Super-FRS Experiment Collaboration

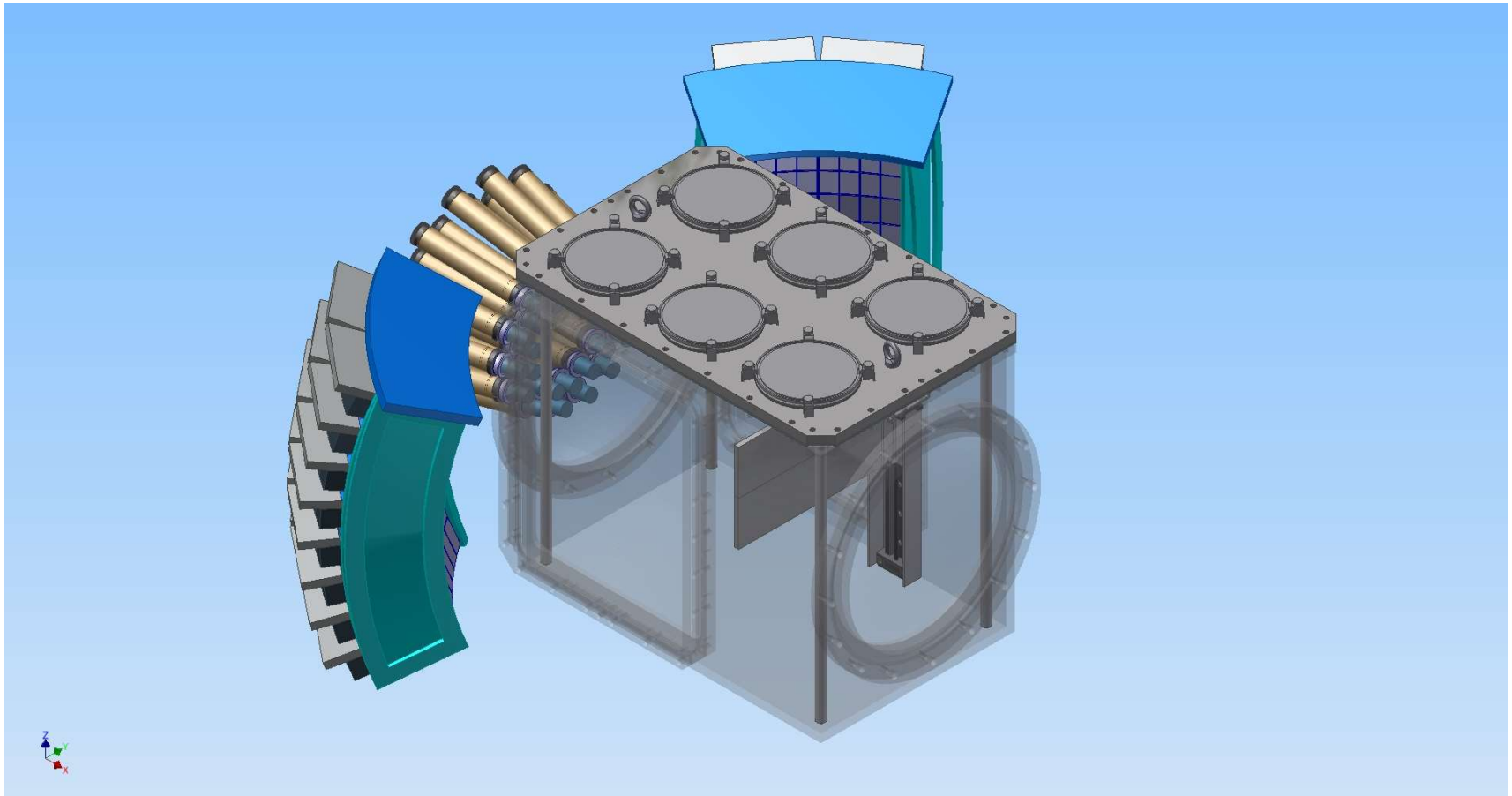


Si TOF detectors



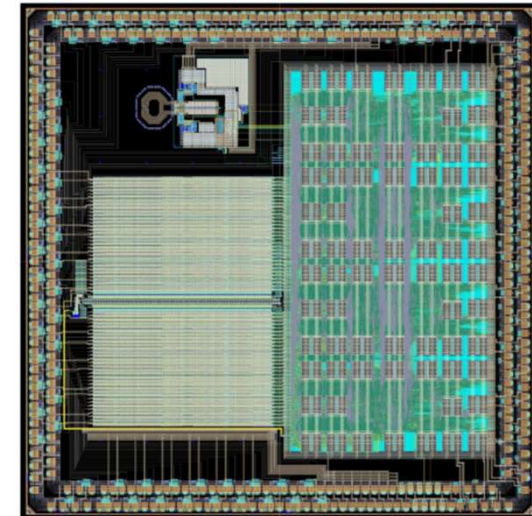


# Vacuum chamber for the EXPERT detectors



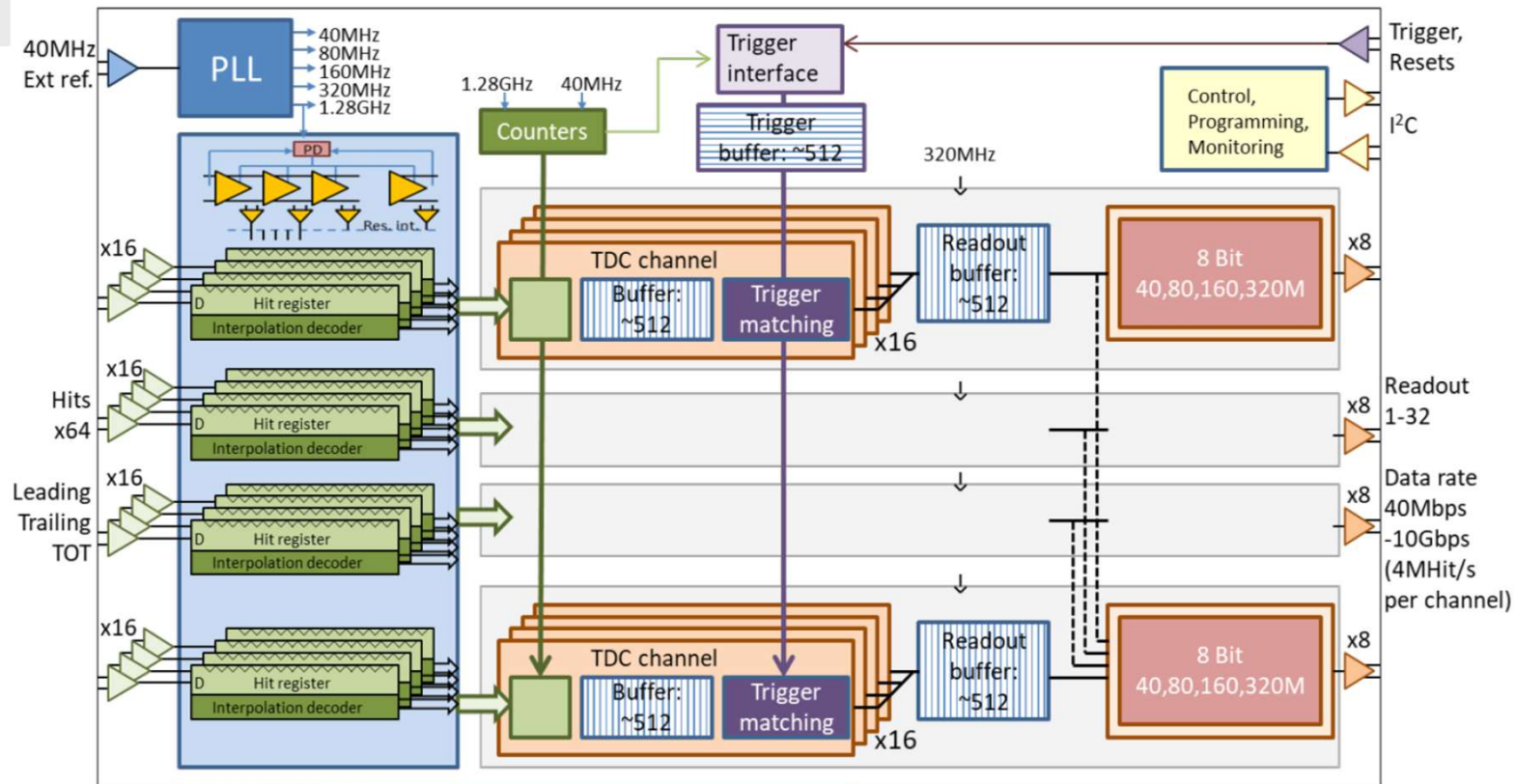
# New TDC for Si TOF detectors

- PicoTDC: Pico-second TDC
- Based on the design of HPTDC/CERN
- Non-triggered or trigger with configurable latency and length, overlap possible
- **3 ps or 12 ps binning**
- **32 or 64 channels per ASIC**
- 100  $\mu$ s full range
- 25 bit leading edge measurement
- Time-over-Threshold measurement



*Jorgen Christiansen, Moritz Horstmann, et al. (CERN)*

# New TDC for Si TOF detectors



TDC Architecture (Change: separate trigger FIFO per group)

- Low power consumption – 1 W @ 3 ps/64 ch at event rate – up to 320 MHz/ch
- TSMC 65 nm production technology – rad. hard up to 100 Mrad
- **Cost – 1-2 CHF/ch**
- Limited production – 2018; testing of fist chips by the users – Q2-Q3 2019
- **Possible synergy with the other projects**

# Conclusions

- Si detectors are rather universal – can measure energy, coordinates and time
- Detectors can work in different environment – vacuum (including UHV), air, room and low temperature
- As any of solid state detectors, Si detectors are sensitive to the radiation but this is measurable and predictable
- TOF resolution for the heavy ions can be as low as 15-20 ps ( $\sigma$ )
- Timing of the Si planar detectors can be explained and calculated → predicted
- Feasibility is demonstrated, large-size system can be made